



High-end Power Semiconductor Manufacturer

ZK200A 4000-5000V

Fast Recovery Diode

- Low switching losses
- Low reverse recovery charge High
- power cycling capability



Average forward current		I _{FAV}	197 A			
Repetitive peak reverse voltage		V _{RRM}	4000–5000 V			
Reverse recovery time		t _{rr}	10.00 µs			
V _{RRM} , V	4000	4200	4400	4600	4800	5000
Voltage code	40	42	44	46	48	50
T _j , °C	– 60 – 150					

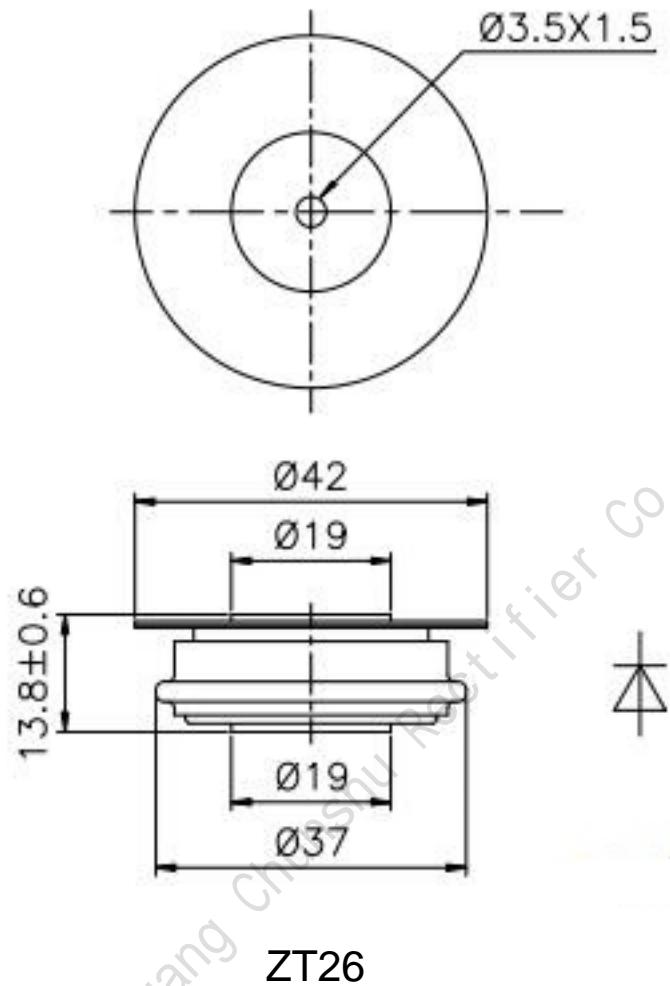
MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions	
ON-STATE					
I _{FAV}	Average forward current	A	197	T _c =85 °C; Double side cooled; 180° half-sine wave; 50 Hz	
I _{FSM}	Surge forward current	kA	2.7	T _j =T _{j max}	180° half-sine wave; t _p =10 ms; V _R =0.6V _{RRM}
I ² t	Safety factor	A ² s·10 ³	36.5	T _j =T _{j max}	180° half-sine wave; t _p =10 ms; V _R =0.6V _{RRM}
BLOCKING					
V _{RRM}	Repetitive peak reverse voltages	V	4000-5000	t _p =10 ms	
V _R	Reverse continuous voltages	V	0.6V _{RRM}	T _j =T _{j max} ;	
 THERMAL					
T _{stg}	Storage temperature	°C	–40–160		
T _j	Operating junction temperature	°C	–60 – 150		
MECHANICAL					
F	Mounting force	kN	3.3– 5.5		

CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions
ON-STATE				
V _{FM}	Peak forward voltage, max	V	3.80	T _j =25 °C; I _{TM} =300A, F=5.0kN
V _{F(TO)}	Forward threshold voltage, max	V	1.95	
r _T	Forward slope resistance, max	mΩ	4.50	T _j =T _{j max} ;
BLOCKING				
I _{RRM}	Repetitive peak reverse current, max	mA	25	T _j =T _{j max} ; V _R =V _{RRM}
SWITCHING				
Q _{rr}	Total recovered charge, max	µC	100	I _{TM} =1000A, t _p =1000µs, -di/dt=60A/µs,
t _{rr}	Reverse recovery time ¹⁾ , max	µs	10.00	V _R =50V
THERMAL				
R _{thjc}	Thermal resistance, junction to case, max	°C/W	0.0800	Clamping force 5.0kN Double side cooled
R _{thck}	Thermal resistance, case to heatsink, max	°C/W	0.0200	Clamping force 5.0kN Double side cooled
MECHANICAL				
w	Weight, max	g	60	

OVERALL DIMENSIONS



All dimensions in millimeters